

Modulating Interfacial Reactions to Develop “Soft” p-CMP Processes

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Lewis University

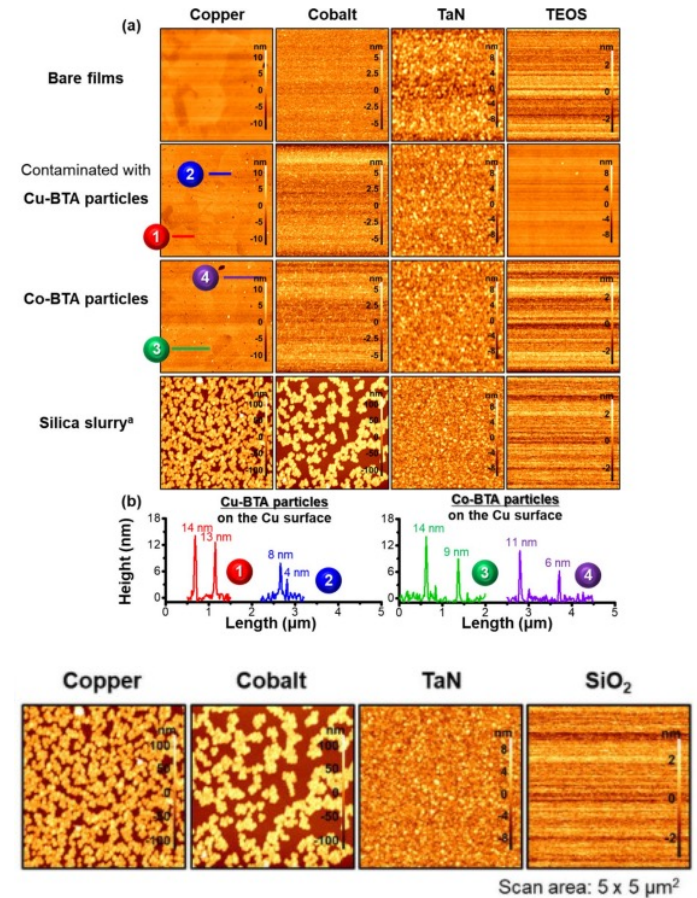
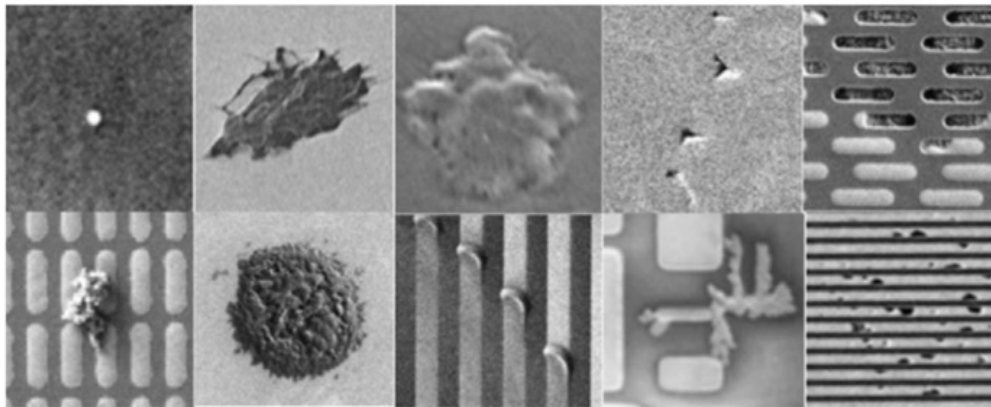
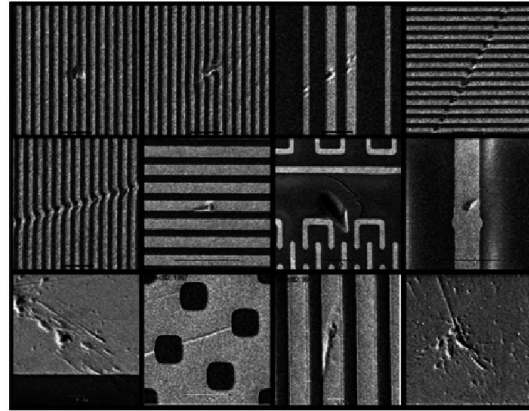
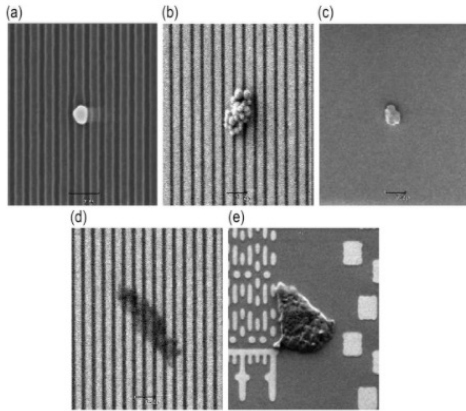
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W.-T. Tseng, in *Advances in Chemical Mechanical Planarization (CMP)*, 2016

Jihoon Seo DOI: 10.5772/intechopen.94292

Chen, Y.; Mikhaylichenko, K.; Brown, B.; Redeker, F. *Post-CMP Cleaning. In Handbook of Silicon Wafer Cleaning Technology; Elsevier Inc., 2018; pp 253–301.*



Post-CMP Cleaning Solutions for the Removal of Organic Contaminants with Reduced Galvanic Corrosion at Copper/Cobalt Interface for Advanced Cu Interconnect Applications

Jihoon Seo,^{1,2,*} S. S. R. K. Hanup Vegi,^{1,*} and S. V. Babu^{1,2,*}

Park, J.; Kim, T. *Fundamentals of Post-CMP Cleaning. 2007, 991.*

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A Breakthrough Method for the Effective Conditioning of PVA Brush Used for Post-CMP Process

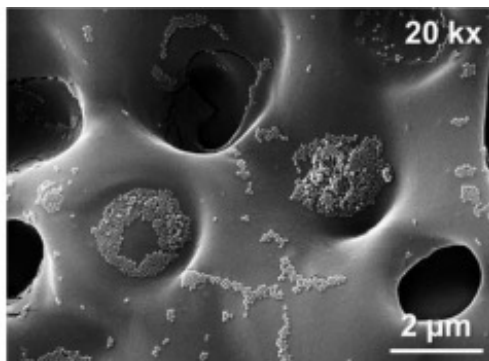
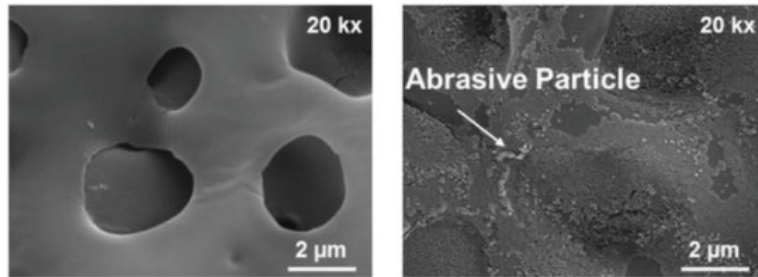
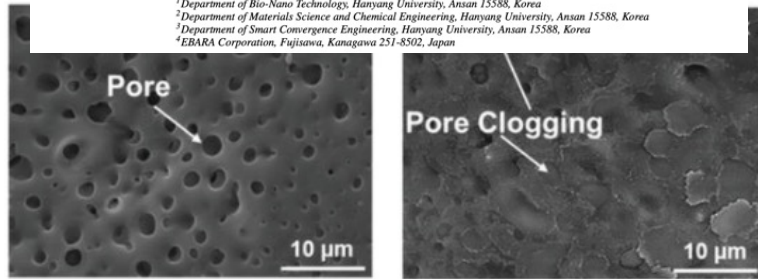
Jung-Hwan Lee,¹ Heon-Yul Ryu,¹ Jun-Kil Hwang,¹ Nagendra Prasad Yerriboina,² Tae-Gon Kim,³ Satomi Hamada,⁴ Yutaka Wada,⁴ Hirokuni Hiyama,⁴ and Jin-Goo Park^{1,2,*}

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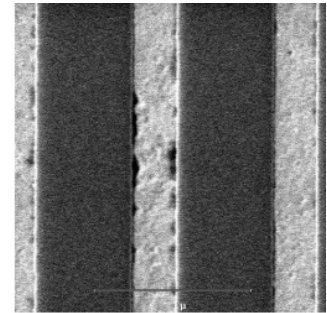
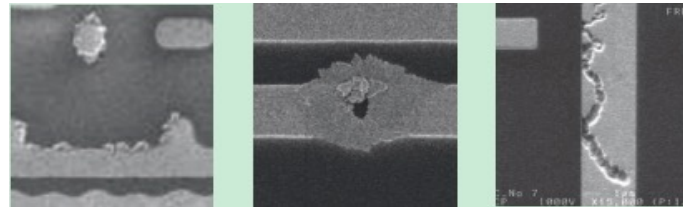
²Department of Materials Science and Chemical Engineering, Hanyang University, Ansan 15588, Korea

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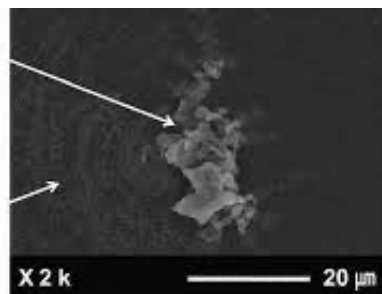
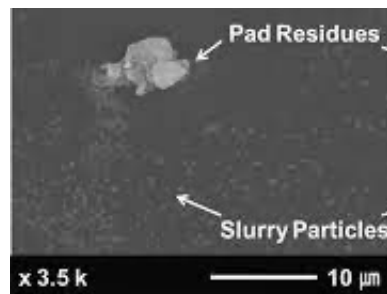
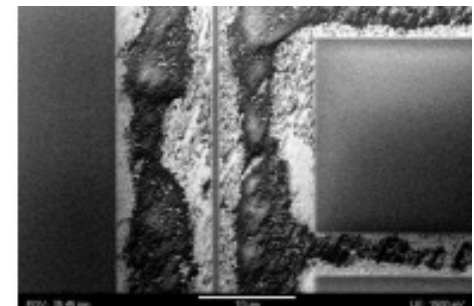
Galvanic Corrosion / Oxidation Defects



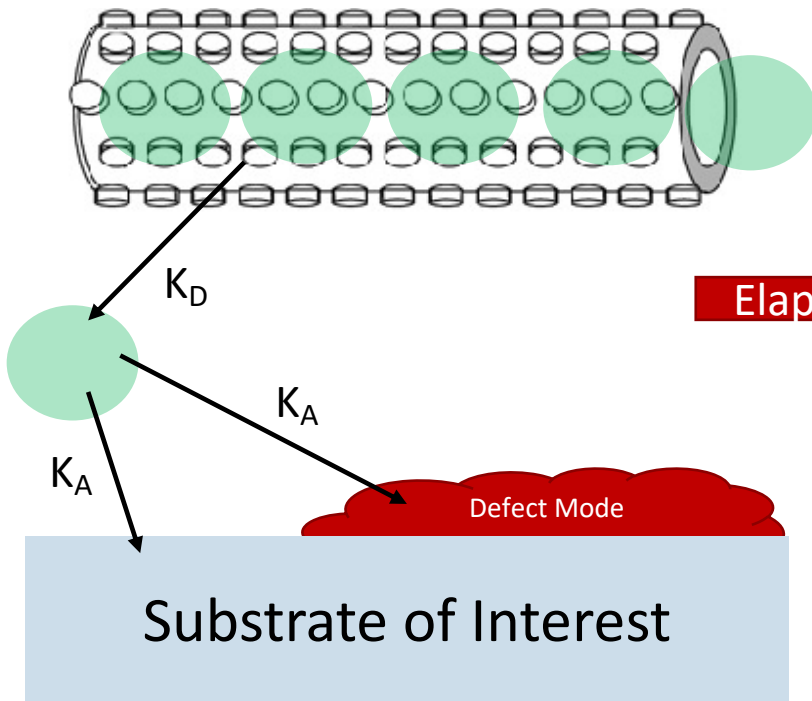
Cleaning Chemistry Residue



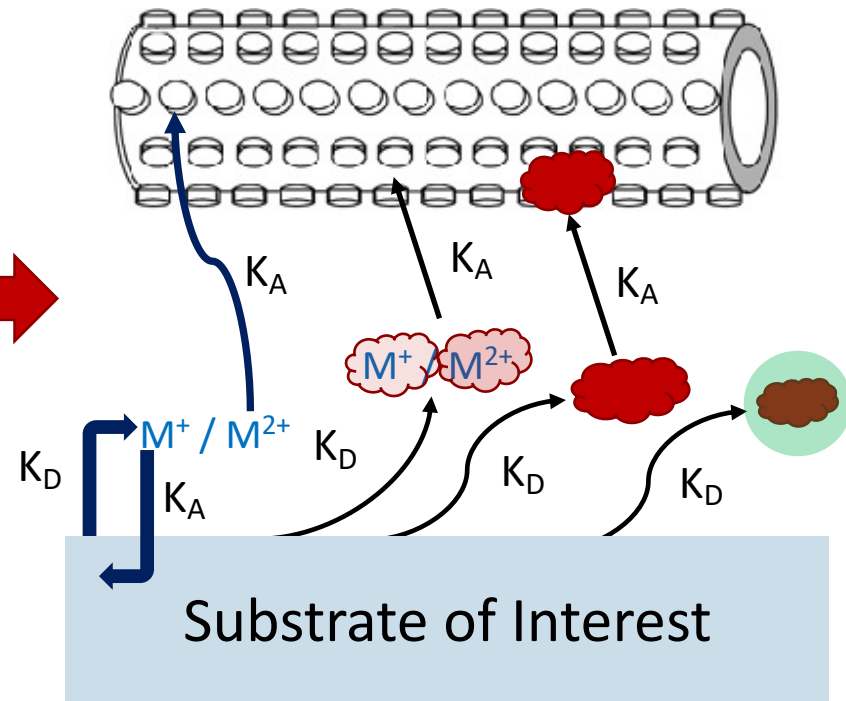
Organic Residue



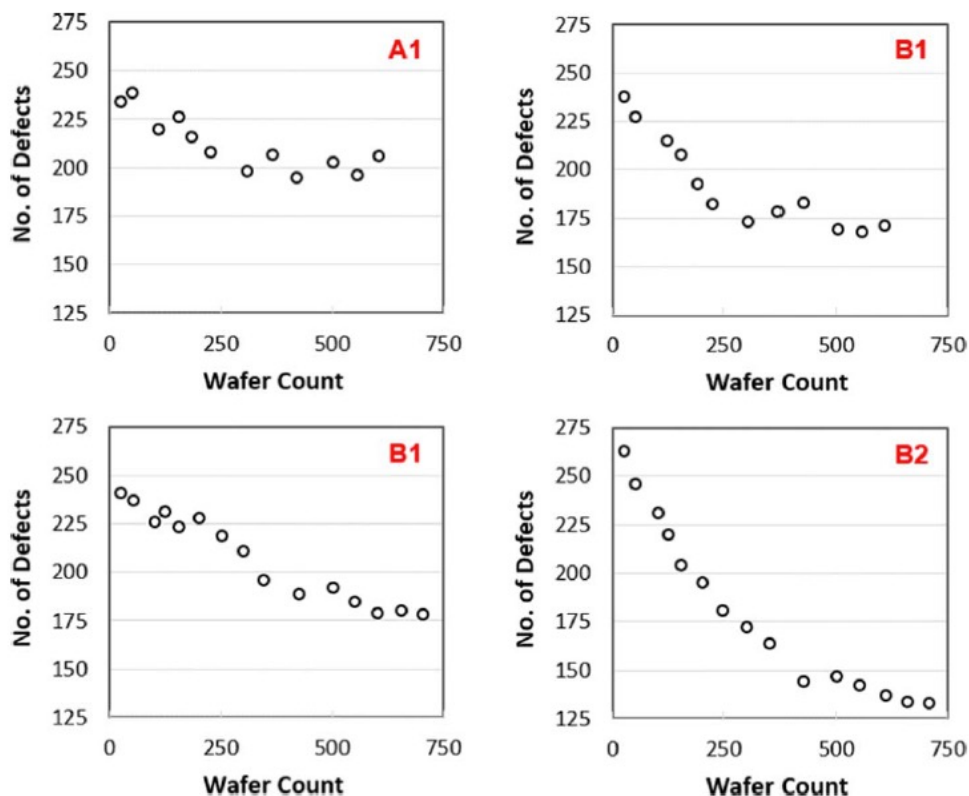
Driving Processes @ $t = 0$



Complex Processes



Raw NADD data for the four marathon tests



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2162-8777/2021/10(6)/064011/10/\$40.00 © 2021 The Electrochemical Society ("ECS"). Published on behalf of ECS by IOP Publishing Limited



Understanding the Reasons Behind Defect Levels in Post-Copper-CMP Cleaning Processes with Different Chemistries and PVA Brushes

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"Solution A" Composition

- An organic acid blend formulated for trace metals and residue removal
- A corrosion protectant
- A surfactant to reduce surface tension and improve lubrication
- Final pH of appx. 2

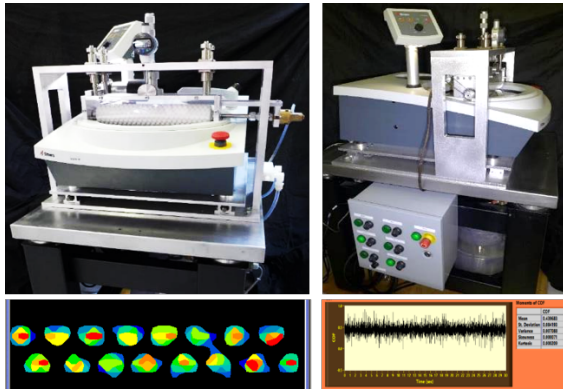
"Solution B" Composition

- An organic acid intended to remove trace metals and residue
- Same surfactant as Solution A, but at twice the concentration
- A polymer that was specifically added to further remove particles and trace metals
- An organic pH adjuster that further aided in particle removal
- Final pH of appx. 11

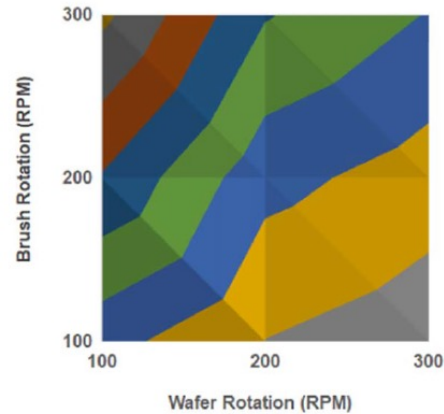
Standard HVM Brushes

In both cases, the PVA was first set to a height such that it just barely contacted the wafer surface. Next, it was pressed towards the wafer by exactly 2mm, and locked in position. Prior to any tests, the brush was broken in for an hour with the wafer and brush rotating at 300 and 300 RPM, respectively.

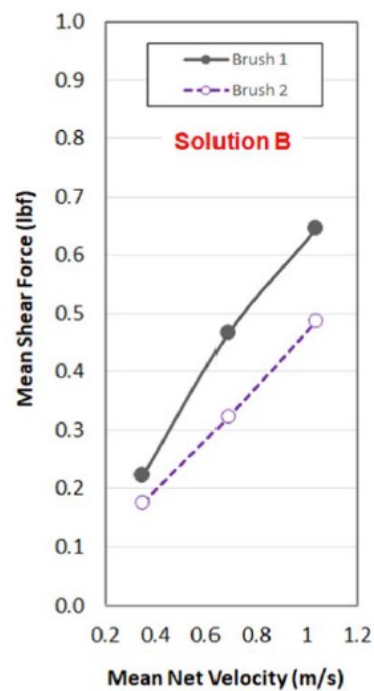
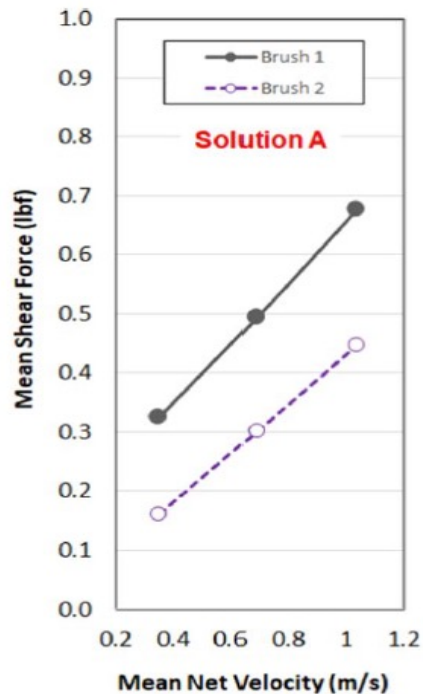
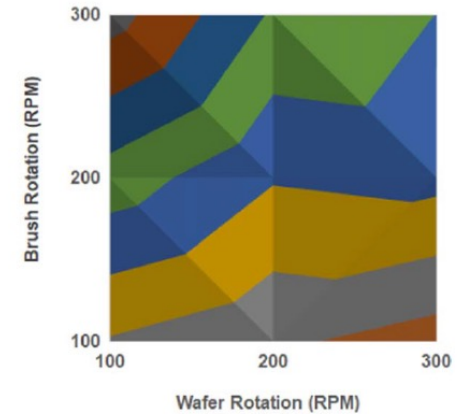
PCC-300® PVA Brush Scrubber and Tribometer



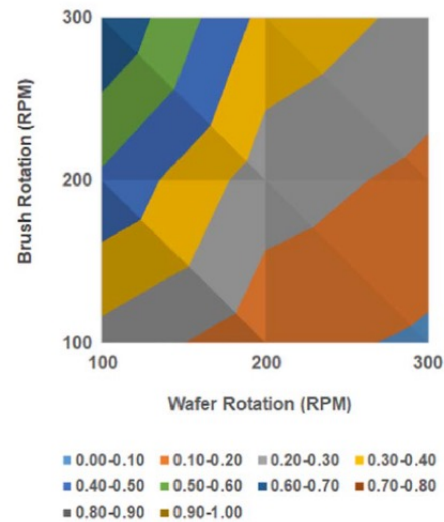
Brush 1 – Solution A



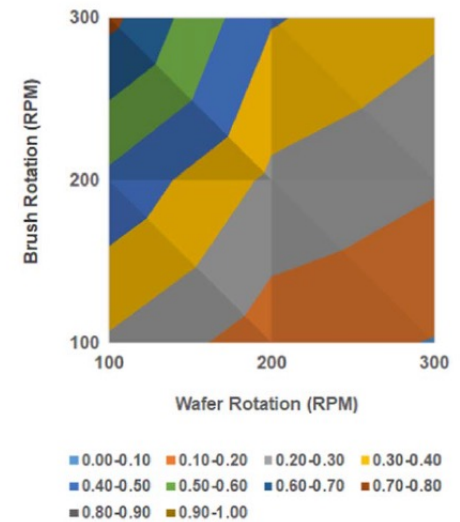
Brush 1 – Solution B



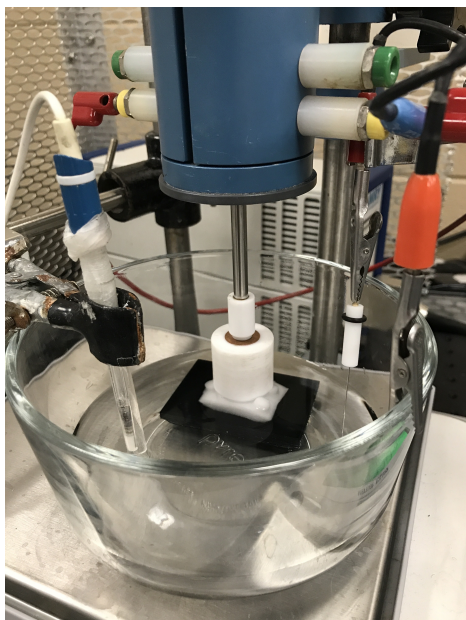
Brush 2 – Solution A



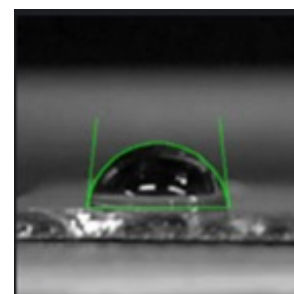
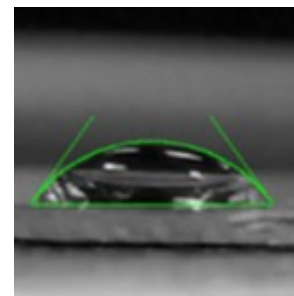
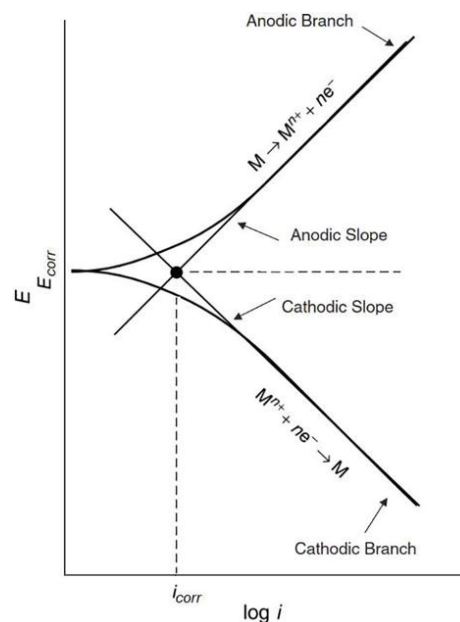
Brush 2 – Solution B



How can we probe brush/chemistry using electrochemistry?



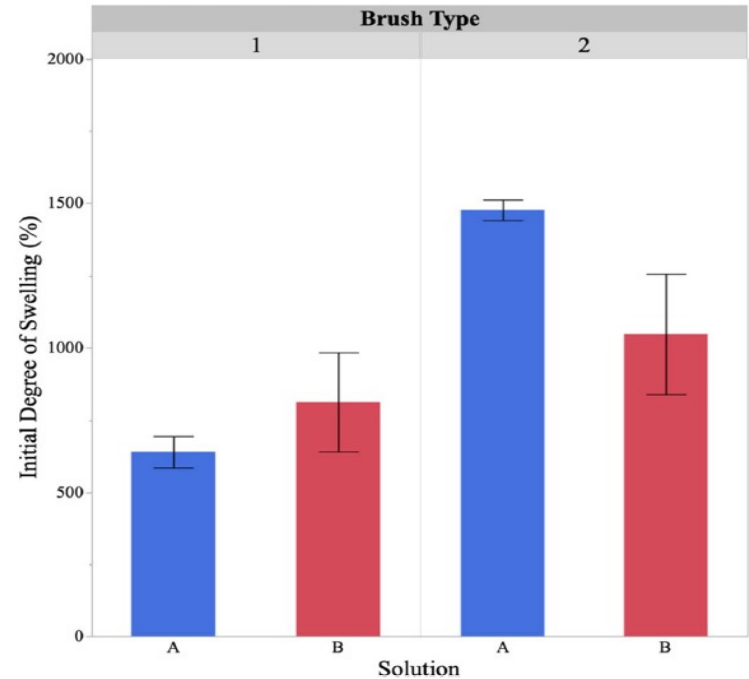
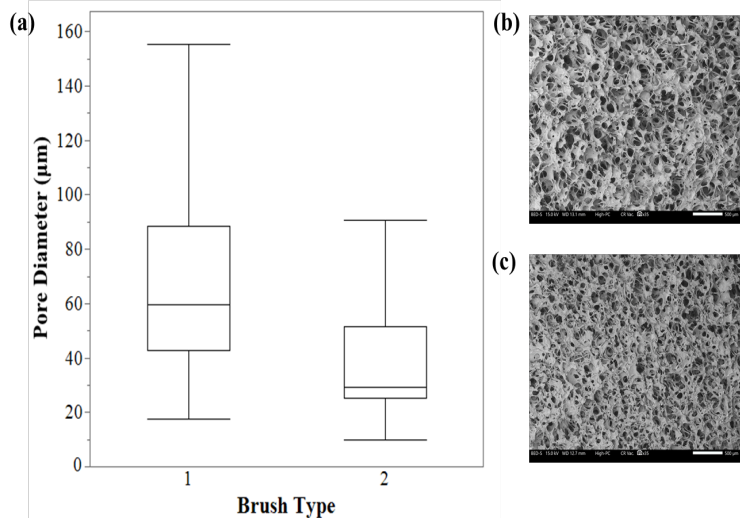
1.0 psi
50 RPM


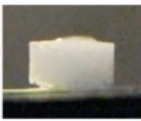
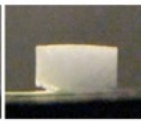












	<u>I_{corr} (μA)</u>	
	Brush 1	Brush 2
Solution A	7.5 ± 1.1	10.8 ± 1.9
Solution B	3.3 ± 1.1	20.5 ± 3.9

Does this argument of surface interactions correlate or even hold true?

Results show Brush 2 has lower SF and significant reduced defects in HVM marathon.



	Solution A			Solution B		
Brush 1						
	33.7 \pm 2.4			42.8 \pm 4.2		
Brush 2						
	27.7 \pm 2.8			29.3 \pm 3.4		

Brush 2 shows smaller pores, slower diffusion of chemistry into the brush matrix, and increased surface chemical activity. All of this is believed to improve particle/defect removal albeit with lower SF.

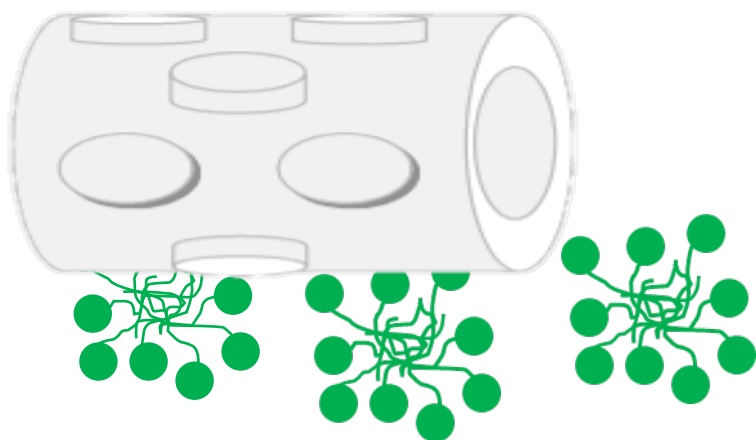


Striking a balance: Role of supramolecular assemblies on the modulation of the chemical and mechanical contributions during Post-STI CMP cleaning

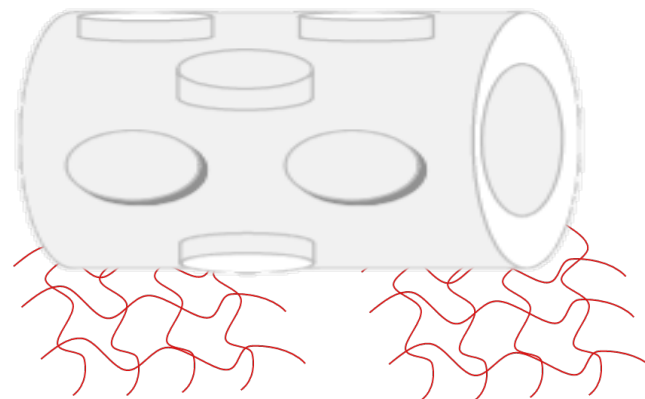
Carolyn F. Graverson^a, Katherine M. Wortman-Otto^a, Abigail N. Linhart^a, Yasa Sampurno^b, Ara Philipossian^b, Jason J. Keleher^{a,*}

^a Department of Chemistry, Lewis University, Romeoville, IL, 60446, USA

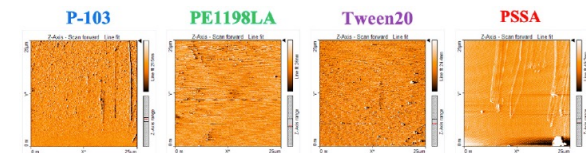
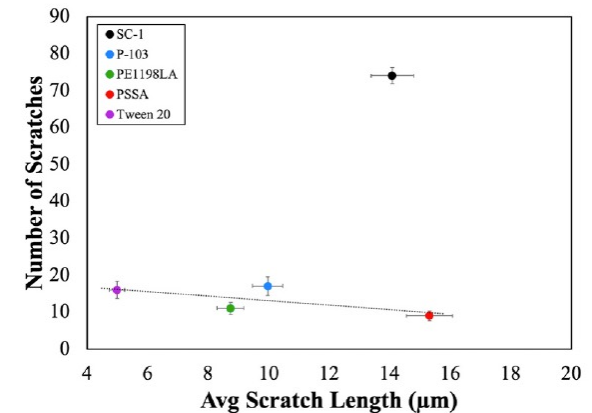
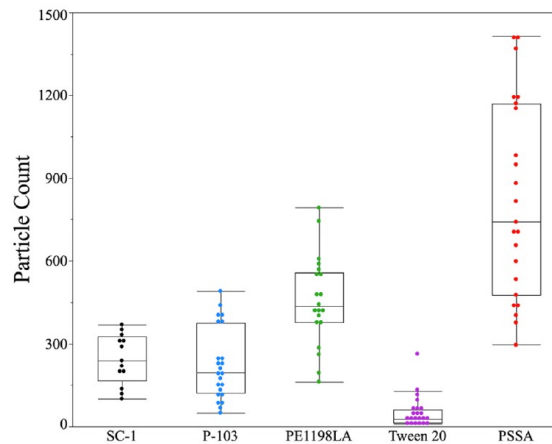
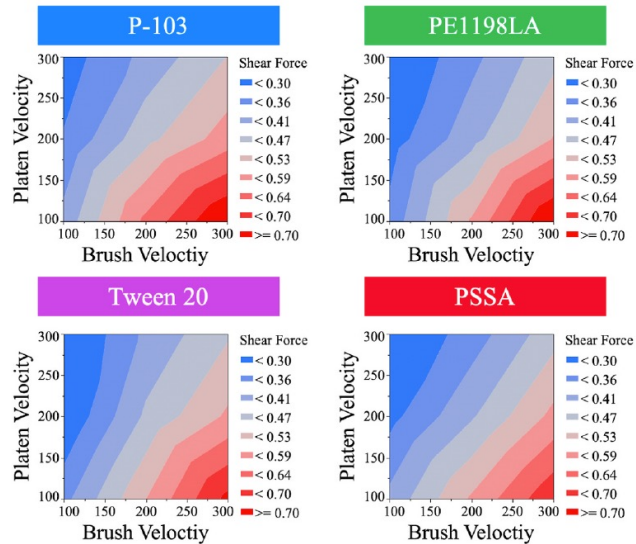
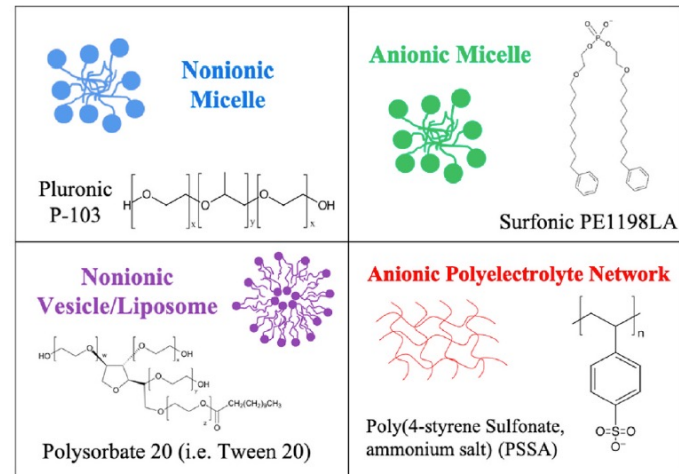
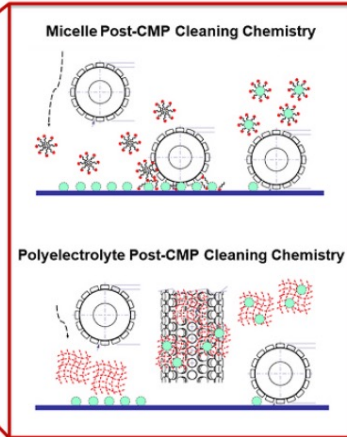
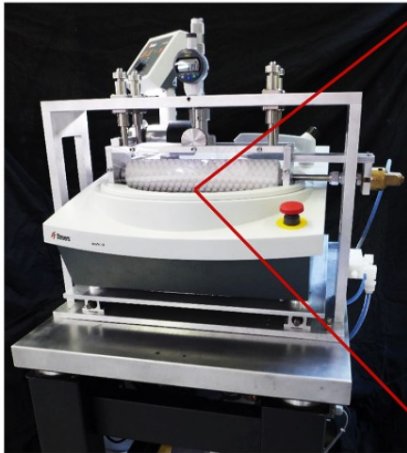
^b Araca, Inc, Tucson, AZ, 85718, USA



Surfactant



Polyelectrolyte



KRG Team!!!



Past and Present Research Collaborators



"Exploring mechanisms to drive innovation for next generation manufacturing..."